

DESCRIPTION

2SA1364 is a silicon PNP epitaxial type transistor. It designed with high voltage, high collector current and high collector dissipation.

Complementary with 2SC3444.

FEATURE

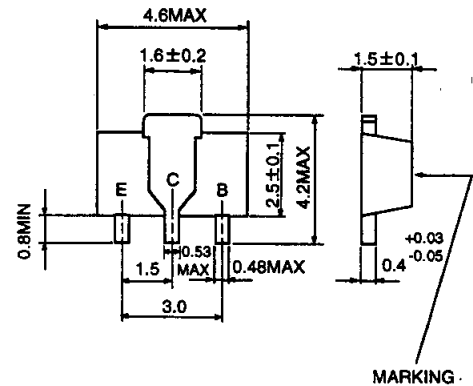
- High voltage $V_{CE0}=-60V$
- High collector current ($I_C=-1A$)
- Small collector to emitter saturation voltage
 $V_{CE(sat)}=-0.11V$ typ(@ $I_C=-500mA$, $I_B=-25mA$)
- High collector dissipation $P_C=500mW$
- Small package for mounting

APPLICATION

Audio machine, VCR, relay drive of other electronic machine, power supply.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

E : EMITTER
C : COLLECTOR
B : BASE

EIAJ : SC-62
JEDEC : -

Note)

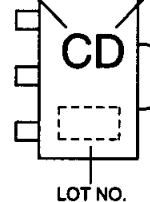
The dimension without tolerance represent central value.

MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector to Base voltage	-60	V
V_{EBO}	Emitter to Base voltage	-6	V
V_{CEO}	Collector to Emitter voltage	-60	V
I_{CM}	Peak Collector current	-2	A
I_C	Collector current	-1	A
P_C	Collector dissipation(Ta=25°C)	500	mW
T_J	Junction temperature	+150	°C
T_{stg}	Storage temperature	-55 to +150	°C

MARKING

TYPE NAME hFE ITEM



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C=-10\mu A, I_E=0$	-60			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=-10\mu A, I_C=0$	-6			V
$V_{(BR)CEO}$	C to E break down voltage	$I_C=-2mA, R_{BE}=\infty$	-60			V
I_{CBO}	Collector cut off current	$V_{CB}=-50V, I_E=0$			-0.2	μA
I_{EBO}	Emitter cut off current	$V_{EB}=-4V, I_C=0$			-0.2	μA
h_{FE}^*	DC forward current gain	$V_{CE}=-4V, I_C=100mA$	55		300	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=-500mA, I_B=-25mA$		-0.11	-0.3	V
f_T	Gain band width product	$V_{CE}=-2V, I_E=10mA$		85		MHz
C_{ob}	Collector output capacitance	$V_{CB}=-10V, I_E=0, f=1MHz$		22		pF

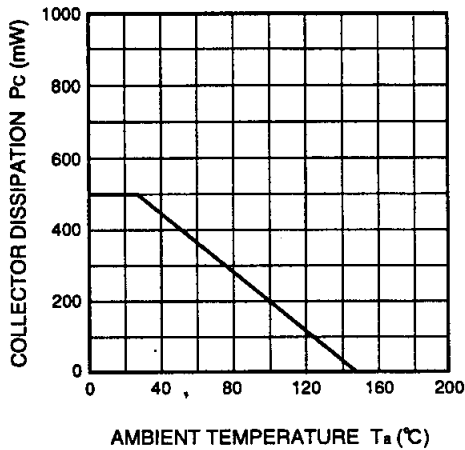
* : It shows hFE classification in right table.

Marking	CC	CD	CE
hFE	55 to 110	90 to 180	150 to 300

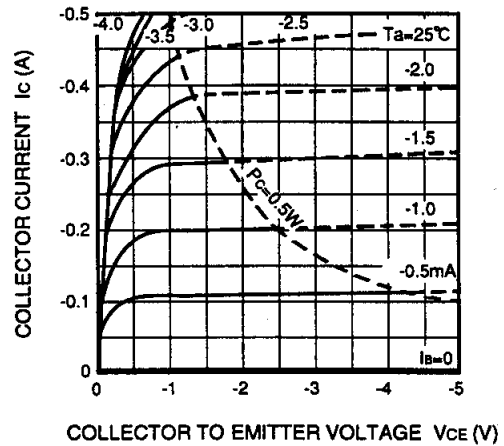
FOR LOW FREQUENCY POWER AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

TYPICAL CHARACTERISTICS

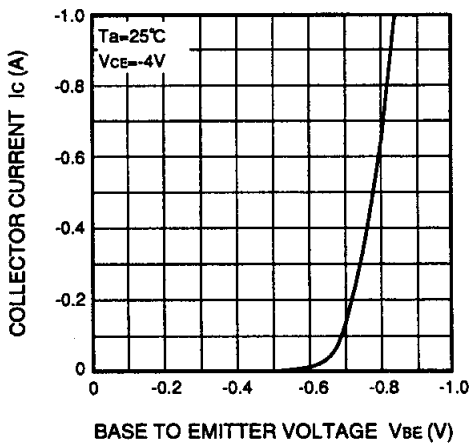
**COLLECTOR DISSIPATION VS.
AMBIENT TEMPERATURE**



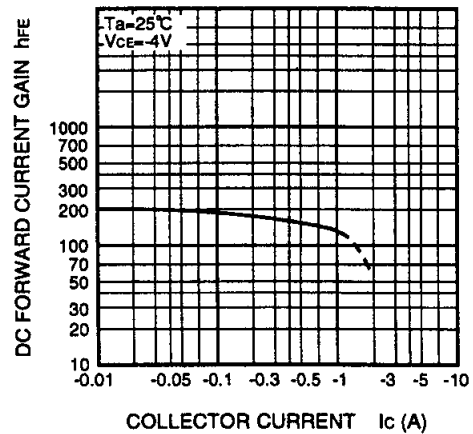
COMMON EMITTER OUTPUT



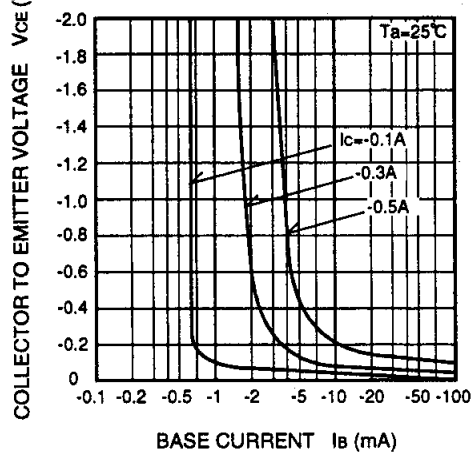
COMMON EMITTER TRANSFER



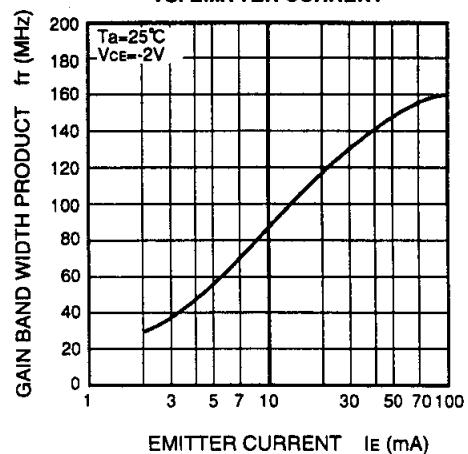
**DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT**



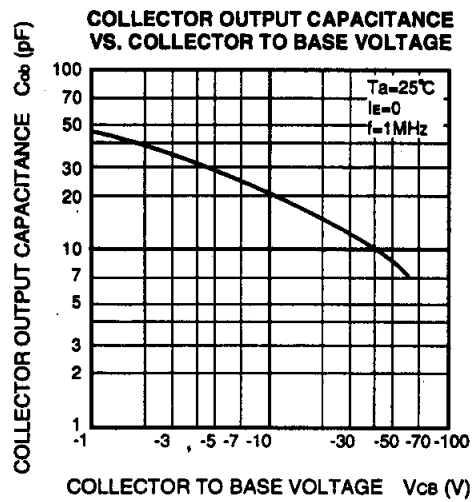
**COLLECTOR TO EMITTER SATURATION
VOLTAGE VS. BASE CURRENT**



**GAIN BAND WIDTH PRODUCT
VS. EMITTER CURRENT**



FOR LOW FREQUENCY POWER AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE





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